In The Specification

Paragraph 0017 has been amended as follows:

Only In the wafer blade for picking up or delivering wafers, the strain sensor may be a piezoelectric sensing device, or may be a sensor that is sensitive to at least μ m strain displacement. The blade body may be formed in the shape of a fork, or may be formed in the shape of a rectangle. The blade body may be formed of metal or ceramic. The strain sensor may be provided in the shape of a thin film.

Paragraph 0036 has been amended as follows:

The strain sensor utilized by the present invention can be any type of sensor that is provided in a thin film configuration. The strain sensor should be sensitive to very small strains displacement, such as strains displacement as small as 1 μ m. One of such suitable strain sensors to be utilized by the present invention wafer blade may be a piezoelectric thin film sensor. When the piezoelectric thin film sensor makes a

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mechanical contact with a surface, an electric field is produced and a signal in the form of an electrical current can be amplified and sent to an alarm panel.

Paragraph 0039 has been amended as follows:

The sensitivity of the piezoelectric thin film sensor 70 must be such that any minute mechanical contact with a wafer below the wafer blade during operation can be detected. For instance, a strain displacement caused by the contact force as small as 1 μ m should be detected and an electric field amplified to produce an electrical signal for the alarm panel 80 shown in Figure 4.